



SBOS177D - NOVEMBER 2000 - REVISED MAY 2005

# Low-Noise, Low-Distortion INSTRUMENTATION AMPLIFIER

## **FEATURES**

- LOW NOISE: 1nV/\Hz at 1kHz
- LOW THD+N: 0.002% at 1kHz, G = 100
- WIDE BANDWIDTH: 800kHz at G = 100
- WIDE SUPPLY RANGE: ±4.5V to ±18V
- HIGH CMR: > 100dB
- GAIN SET WITH EXTERNAL RESISTOR
- SO-14 SURFACE-MOUNT PACKAGE

# **APPLICATIONS**

- PROFESSIONAL MICROPHONE PREAMPS
- MOVING-COIL TRANSDUCER AMPLIFIERS
- DIFFERENTIAL RECEIVERS
- BRIDGE TRANSDUCER AMPLIFIERS

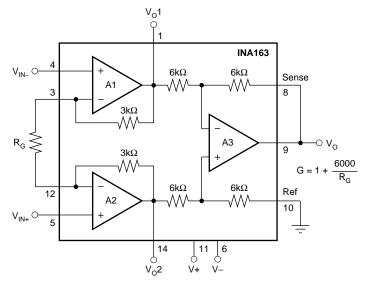
# DESCRIPTION

The INA163 is a very low-noise, low-distortion, monolithic instrumentation amplifier. Its current-feedback circuitry achieves very wide bandwidth and excellent dynamic response over a wide range of gain. It is ideal for low-level audio signals such as balanced lowimpedance microphones. Many industrial, instrumentation, and medical applications also benefit from its low noise and wide bandwidth.

Unique distortion cancellation circuitry reduces distortion to extremely low levels, even in high gain. The INA163 provides near-theoretical noise performance for 200 $\Omega$  source impedance. Its differential input, low noise, and low distortion provide superior performance in professional microphone amplifier applications.

The INA163's wide supply voltage, excellent output voltage swing, and high output current drive allow its use in high-level audio stages as well.

The INA163 is available in a space-saving SO-14 surface-mount package, specified for operation over the  $-40^{\circ}$ C to  $+85^{\circ}$ C temperature range.



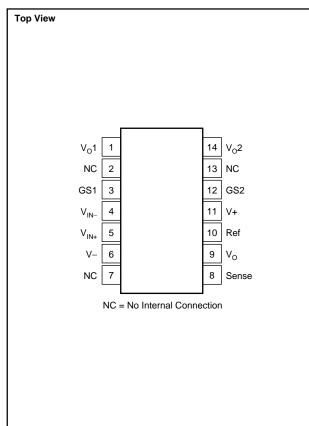


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#### PIN CONFIGURATION



# ELECTROSTATIC DISCHARGE SENSITIVITY

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### ABSOLUTE MAXIMUM RATINGS(1)

Power Supply Voltage	±18V
Signal Input Terminals, Voltage <sup>(2)</sup>	
Current <sup>(2)</sup>	10mA
Output Short-Circuit to Ground	Continuous
Operating Temperature	–55°C to +125°C
Storage Temperature	–55°C to +125°C
Junction Temperature	+150°C
Lead Temperature (soldering, 10s)	+300°C
Lead Temperature (soldering, TUS)	+300°C

NOTES: (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied. (2) Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current limited to 10mA or less.

#### PACKAGE/ORDERING INFORMATION<sup>(1)</sup>

PRODUCT	PACKAGE-LEAD	DESIGNATOR	MARKING
INA163UA	SO-14 Surface Mount	D	INA163UA

NOTE: (1) For the most current package and ordering information, see the Package Option Addendum located at the end of this document, or see the TI web site at www.ti.com.



# ELECTRICAL CHARACTERISTICS: V<sub>S</sub> = $\pm 15V$

 $T_A$  = +25°C and at rated supplies,  $V_S$  =  $\pm 15V,~R_L$  = 2k $\Omega$  connected to ground, unless otherwise noted.

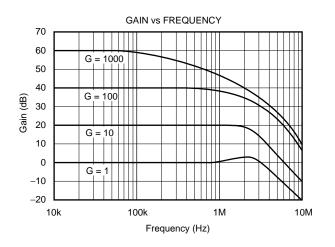
PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNITS	
GAIN						
Range			1 to 10000		V/V	
Gain Equation <sup>(1)</sup>			$G = 1 + 6k/R_{G}$			
Gain Error, G = 1			±0.1	±0.25	%	
G = 10			±0.2	±0.7	%	
G = 100 G = 100			±0.2	10.1	%	
G = 100 G = 1000					%	
			±0.5	110		
Gain Temp Drift Coefficient, G = 1			±1	±10	ppm/°C	
G > 10			±25	±100	ppm/°C	
Nonlinearity, G = 1			±0.0003		% of FS	
G = 100			±0.0006		% of FS	
INPUT STAGE NOISE						
Voltage Noise	$R_{SOURCE} = 0\Omega$					
$f_0 = 1 \text{ kHz}$			1		nV/√Hz	
$f_0 = 100$ Hz			1.2		nV/√Hz	
-					nV/√Hz	
$f_0 = 10Hz$			2		IIV/VHZ	
Current Noise						
$f_{O} = 1 \text{kHz}$			0.8		pA/√Hz	
OUTPUT STAGE NOISE						
Voltage Noise, f <sub>O</sub> = 1kHz			60		nV/√Hz	
INPUT OFFSET VOLTAGE						
Input Offset Voltage	$V_{CM} = V_{OUT} = 0V$		50 + 2000/G	250 + 5000/G	μV	
vs Temperature	$T_A = T_{MIN}$ to $T_{MAX}$		1 + 20/G	200 / 0000/0	μV/°C	
vs Power Supply	$V_{\rm S} = \pm 4.5 \text{V} \text{ to } \pm 18 \text{V}$		1 + 50/G	3 + 200/G	μV/ 0 μV/V	
	v <sub>S</sub> = ±4.5 v to ±18 v		1 + 30/G	3 + 200/G	μν/ν	
INPUT VOLTAGE RANGE						
Common-Mode Voltage Range	$V_{IN+} - V_{IN-} = 0V$	(V+) – 4	(V+) – 3		V	
	$V_{IN+} - V_{IN-} = 0V$	(V–) + 4	(V–) + 3		V	
Common-Mode Rejection, G = 1	$V_{CM} = \pm 11V, R_{SRC} = 0\Omega$	70	80		dB	
G = 100		100	116		dB	
INPUT BIAS CURRENT						
Initial Bias Current			2	12	μA	
			10	12	μΑ nA/°C	
vs Temperature						
Initial Offset Current			0.1	1	μA	
vs Temperature			0.5		nA/°C	
INPUT IMPEDANCE						
	Differential		60    2		MΩ    pF	
	Common-Mode		60    2		MΩ    pF	
DYNAMIC RESPONSE						
Bandwidth, Small Signal, –3dB, G = 1			3.4			
G = 100			800		kHz	
Slew Rate			15		V/µs	
THD+Noise, f = 1kHz	G = 100		0.002		ν/μs %	
Settling Time, 0.1%	G = 100, 10V Step		2		μs	
0.01%	G = 100, 10V Step		3.5		μs	
Overload Recovery	50% Overdrive		1		μs	
OUTPUT	_					
Voltage	$R_L = 2k\Omega$ to Gnd	(V+) – 2	(V+) – 1.8		V	
		(V–) + 2	(V–) + 1.8		V	
Load Capacitance Stability			1000		pF	
Short-Circuit Current	Continuous-to-Common		±60		mA	
POWER SUPPLY						
Rated Voltage			±15		V	
Voltage Range		±4.5	±10	±18	v	
Current, Quiescent	$I_{O} = 0mA$	<u>_</u> 4.3	±10	±10 ±12	mA	
	1 <sub>0</sub> = 011A		-10	±14	IIIA	
Specification		-40		+85	°C	
Operating		-40		+125	°C	
$ heta_{JA}$			100		°C/W	

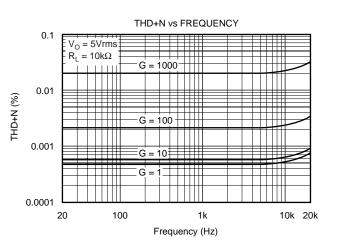
NOTE: (1) Gain accuracy is a function of external  $R_G$ .

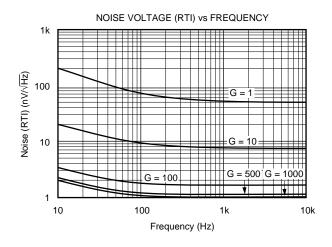


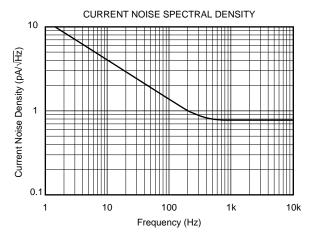
# **TYPICAL CHARACTERISTICS**

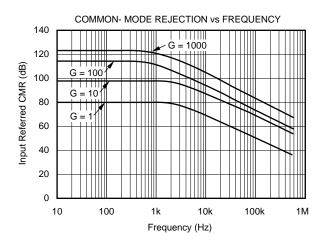
At T\_A = +25°C, V\_S = 5V, V\_{CM} = 1/2V\_S, R\_L = 25k\Omega, CL = 50pF, unless otherwise noted.

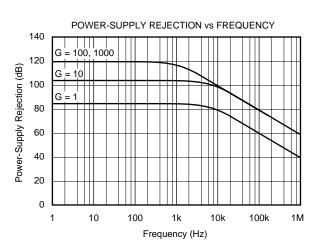








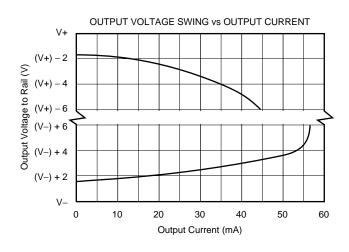


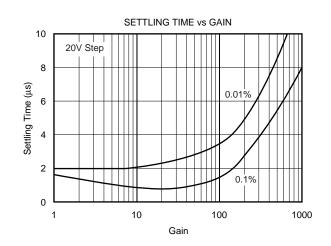


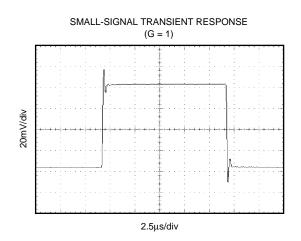


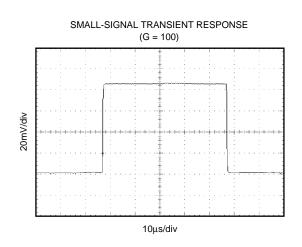
# **TYPICAL CHARACTERISTICS (Cont.)**

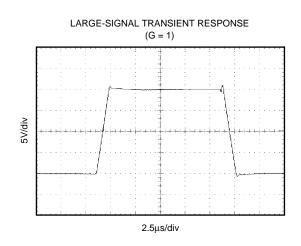
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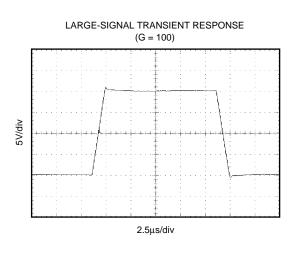














# **APPLICATIONS INFORMATION**

Figure 1 shows the basic connections required for operation. Power supplies should be bypassed with  $0.1\mu$ F tantalum capacitors near the device pins. The output Sense (pin 8) and output Reference (pin 10) should be low-impedance connections. Resistance of a few ohms in series with these connections will degrade the common-mode rejection of the INA163.

### GAIN-SET RESISTOR

Gain is set with an external resistor,  $R_G$ , as shown in Figure 1. The two internal  $3k\Omega$  feedback resistors are laser-trimmed to  $3k\Omega$  within approximately ±0.2%. Gain is:

$$G = 1 + \frac{6000}{R_G}$$

The temperature coefficient of the internal  $3k\Omega$  resistors is approximately  $\pm 25$  ppm/°C. Accuracy and TCR of the external R<sub>G</sub> will also contribute to gain error and

temperature drift. These effects can be inferred from the gain equation. Make a short, direct connection to the gain set resistor,  $R_G$ . Avoid running output signals near these sensitive input nodes.

### NOISE PERFORMANCE

The INA163 provides very low-noise with low-source impedance. Its  $1nV/\sqrt{Hz}$  voltage noise delivers near-theoretical noise performance with a source impedance of  $200\Omega$ . The input stage design used to achieve this low noise, results in relatively high input bias current and input bias current noise. As a result, the INA163 may not provide the best noise performance with a source impedance greater than  $10k\Omega$ . For source impedance greater than  $10k\Omega$ , other instrumentation amplifiers may provide improved noise performance.

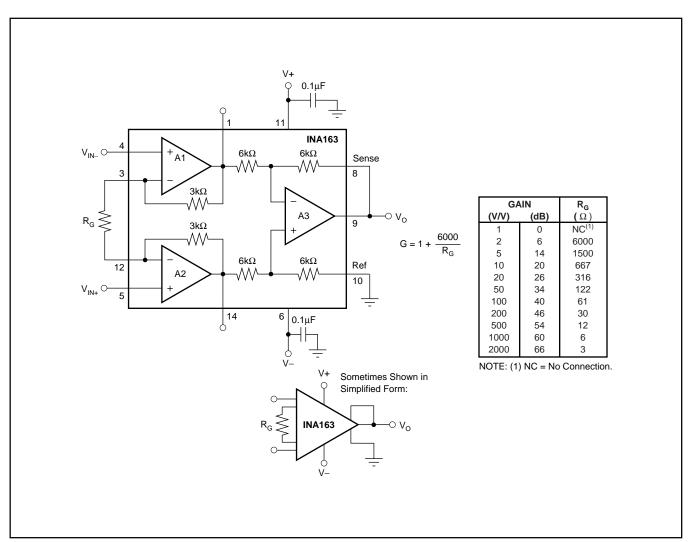


FIGURE 1. Basic Circuit Connections.

#### INPUT CONSIDERATIONS

Very low source impedance (less than  $10\Omega$ ) can cause the INA163 to oscillate. This depends on circuit layout, signal source, and input cable characteristics. An input network consisting of a small inductor and resistor, as shown in Figure 2, can greatly reduce any tendency to oscillate. This is especially useful if a variety of input sources are to be connected to the INA163. Although not shown in other figures, this network can be used as needed with all applications shown.

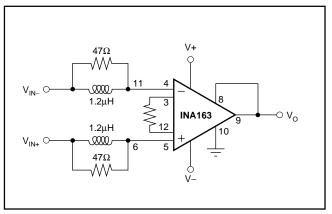


FIGURE 2. Input Stabilization Network.

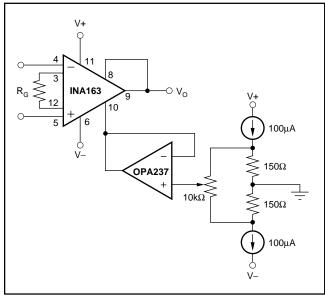


FIGURE 3. Offset Voltage Adjustment Circuit.

#### OFFSET VOLTAGE TRIM

A variable voltage applied to pin 10, as shown in Figure 3, can be used to adjust the output offset voltage. A voltage applied to pin 10 is summed with the output signal. An op amp connected as a buffer is used to provide a low impedance at pin 10 to assure good common-mode rejection.

#### **OUTPUT SENSE**

An output sense terminal allows greater gain accuracy in driving the load. By connecting the sense connection at the load,  $I \cdot R$  voltage loss to the load is included inside the feedback loop. Current drive can be increased by connecting a buffer amp inside the feedback loop, as shown in Figure 4.

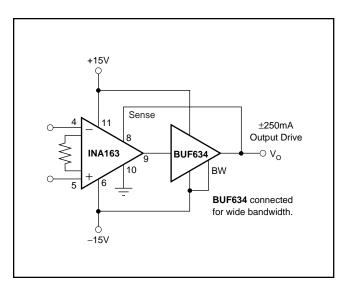


FIGURE 4. Buffer for Increase Output Current.



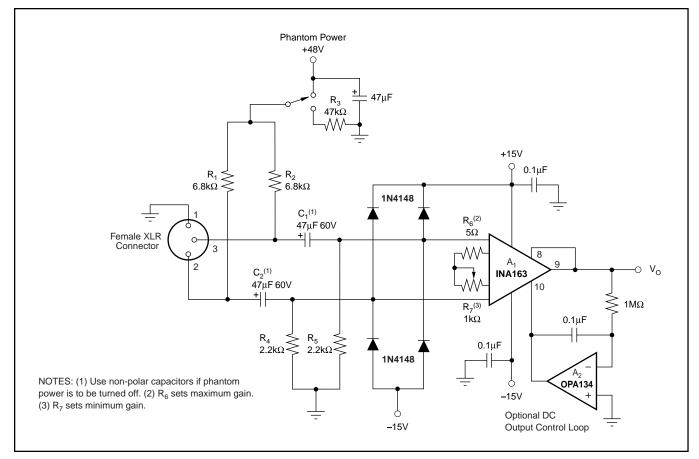


FIGURE 5. Phantom-Powered Microphone Preamplifier.

#### **MICROPHONE AMPLIFIER**

Figure 5 shows a typical circuit for a professional microphone input amplifier.  $R_1$  and  $R_2$  provide a current path for conventional 48V phantom power source for a remotely located microphone. An optional switch allows phantom power to be disabled.  $C_1$  and  $C_2$  block the phantom power voltage from the INA163 input circuitry. Non-polarized capacitors should be used for  $C_1$  and  $C_2$  if phantom power is to be disabled. For additional input protection against ESD and hot-plugging, four INA4148 diodes may be connected from the input to supply lines.

 $R_4$  and  $R_5$  provide a path for input bias current of the INA163. Input offset current (typically 100nA) creates a DC differential input voltage that will produce an output

offset voltage. This is generally the dominant source of output offset voltage in this application. With a maximum gain of 1000 (60dB), the output offset voltage can be several volts. This may be entirely acceptable if the output is AC-coupled into the subsequent stage. An alternate technique is shown in Figure 5. An inexpensive FET-input op amp in a feedback loop drives the DC output voltage to 0V.  $A_2$  is not in the audio signal path and does not affect signal quality.

Gain is set with a variable resistor,  $R_7$ , in series with  $R_6$ .  $R_6$  determines the maximum gain. The total resistance,  $R_6 + R_7$ , determines the lowest gain. A special reverse-log taper potentiometer for  $R_7$  can be used to create a linear change (in dB) with rotation.



#### **PACKAGING INFORMATION**

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
INA163UA	Active	Production	SOIC (D)   14	50   TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	INA163UA
INA163UA.A	Active	Production	SOIC (D)   14	50   TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	INA163UA
INA163UA/2K5	Active	Production	SOIC (D)   14	2500   LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	INA163UA
INA163UA/2K5.A	Active	Production	SOIC (D)   14	2500   LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	INA163UA

<sup>(1)</sup> **Status:** For more details on status, see our product life cycle.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

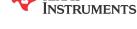
<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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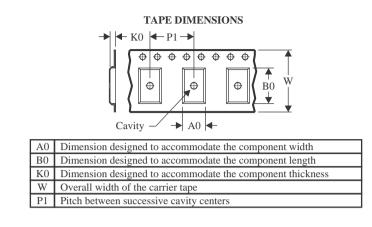


Texas

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### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal	

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA163UA/2K5	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1



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## PACKAGE MATERIALS INFORMATION

24-Jul-2025



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA163UA/2K5	SOIC	D	14	2500	353.0	353.0	32.0

### TEXAS INSTRUMENTS

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### TUBE



## - B - Alignment groove width

\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
INA163UA	D	SOIC	14	50	506.6	8	3940	4.32
INA163UA.A	D	SOIC	14	50	506.6	8	3940	4.32

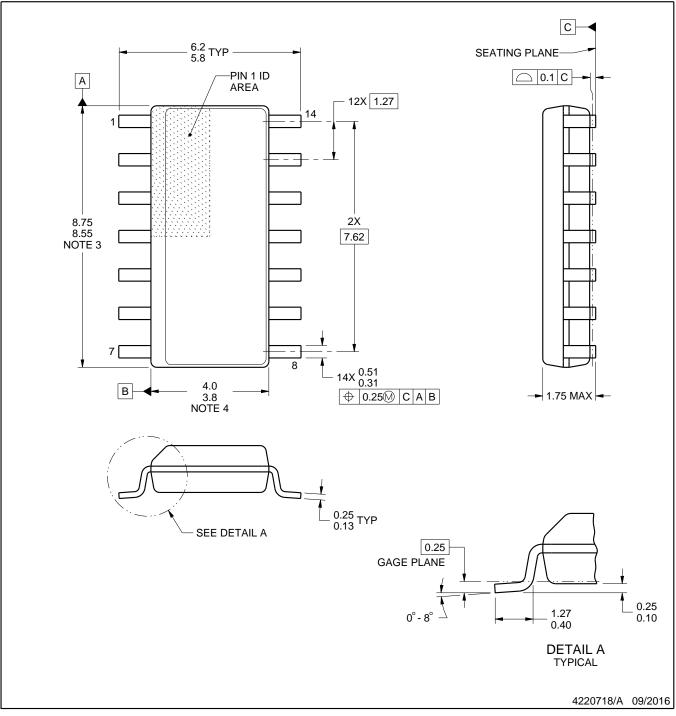
# **D0014A**



## **PACKAGE OUTLINE**

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.

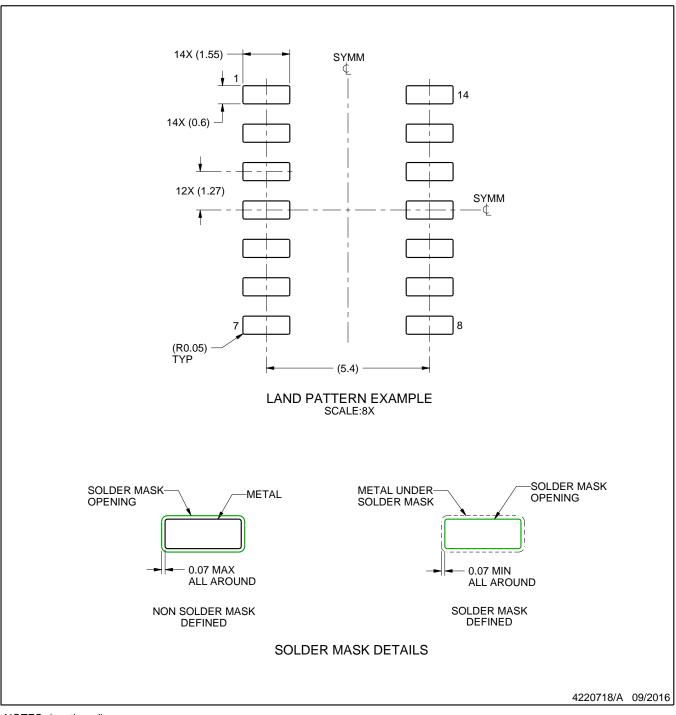


## D0014A

# **EXAMPLE BOARD LAYOUT**

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

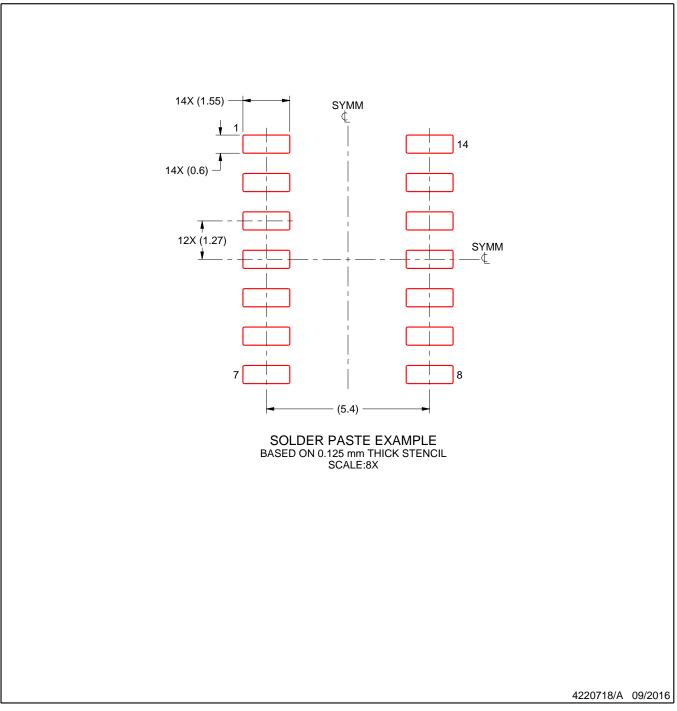


## D0014A

## **EXAMPLE STENCIL DESIGN**

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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